XN0611FH (XN611FH)

Silicon PNP epitaxial planer transistor

For switching/digital circuits

Features

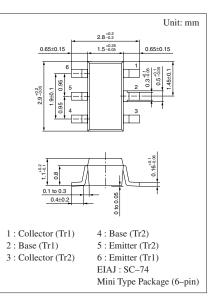
- Two elements incorporated into one package. (Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half.

Basic Part Number of Element

• UNR111F(UN111F) + UNR111H(UN111H)

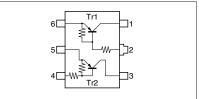
Parameter		Symbol Ratings		Unit	
Tr1	Collector to base voltage	V _{CBO}	-50	V	
	Collector to emitter voltage	V _{CEO}	-50	V	
	Collector current	I _C	-100	mA	
Tr2	Collector to base voltage	V _{CBO}	-50	V	
	Collector to emitter voltage	V _{CEO}	-50	V	
	Collector current	I _C	-100	mA	
Overall	Total power dissipation	P _T	300	mW	
	Junction temperature	Tj	150	°C	
	Storage temperature	T _{stg}	-55 to +150	°C	

Absolute Maximum Ratings (Ta=25°C)



Marking Symbol: 4S

Internal Connection



Note.) The Part number in the Parenthesis shows conventional part number.

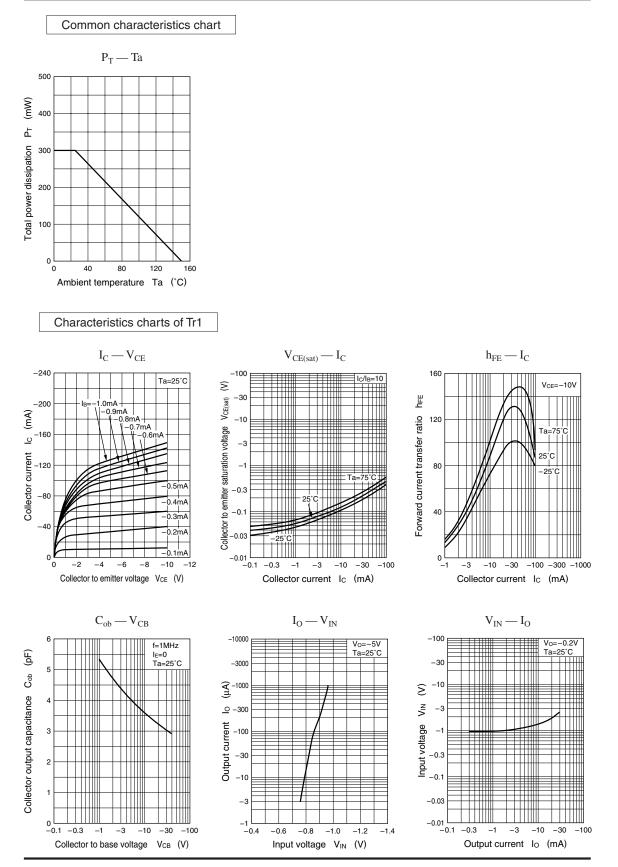
Electrical Characteristics (Ta=25°C)

• Tr1

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V _{CBO}	$I_{\rm C} = -10 \mu A, I_{\rm E} = 0$	-50			V
Collector to emitter voltage	V _{CEO}	$I_C = -2mA$, $I_B = 0$	-50			V
	I _{CBO}	$V_{CB} = -50V, I_E = 0$			- 0.1	μΑ
Collector cutoff current	I _{CEO}	$V_{CE} = -50V, I_B = 0$			- 0.5	μΑ
Emitter cutoff current	I _{EBO}	$V_{EB} = -6V, I_C = 0$			-1.0	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10V, I_C = -5mA$	30			
Collector to emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = -0.3 {\rm mA}$			- 0.25	V
Output voltage high level	V _{OH}	$V_{CC} = -5V, V_B = -0.5V, R_L = 1k\Omega$	-4.9			V
Output voltage low level	V _{OL}	$V_{CC} = -5V, V_B = -2.5V, R_L = 1k\Omega$			- 0.2	V
Transition frequency	f _T	$V_{CB} = -10V, I_E = 1mA, f = 200MHz$		80		MHz
Input resistance	R ₁		-30%	4.7	+30%	kΩ
Resistance ratio	R ₁ /R ₂			0.47		

• Tr2

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector to base voltage	V _{CBO}	$I_{\rm C} = -10\mu A, I_{\rm E} = 0$	-50			V
Collector to emitter voltage	V _{CEO}	$I_{\rm C} = -2mA, I_{\rm B} = 0$	-50			V
	I _{CBO}	$V_{CB} = -50V, I_E = 0$			- 0.1	μΑ
Collector cutoff current	I _{CEO}	$V_{CE} = -50V, I_B = 0$			- 0.5	μΑ
Emitter cutoff current	I _{EBO}	$V_{EB} = -6V, I_C = 0$			- 0.5	mA
Forward current transfer ratio	h _{FE}	$V_{CE} = -10V, I_C = -5mA$	30			
Collector to emitter saturation voltage	V _{CE(sat)}	$I_{C} = -10mA, I_{B} = -0.3mA$			- 0.25	V
Output voltage high level	V _{OH}	$V_{CC} = -5V, V_B = -0.5V, R_L = 1k\Omega$	-4.9			V
Output voltage low level	V _{OL}	$V_{CC} = -5V, V_B = -2.5V, R_L = 1k\Omega$			- 0.2	V
Transition frequency	f _T	$V_{CB} = -10V, I_E = 1mA, f = 200MHz$		80		MHz
Input resistance	R ₁		-30%	2.2	+30%	kΩ
Resistance ratio	R ₁ /R ₂		0.17	0.22	0.27	



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V_{CE}=-10V

25

-3 -10 -30 -100

Characteristics charts of Tr2 $I_C - V_{CE}$ V_{CE(sat)} — I_C $h_{FE} - I_C$ -120 -100 240 $I_C/I_B=10$ Ta=25°C Ξ hFE Collector to emitter saturation voltage VcE(sat) -100 200 Collector current Ic (mA) Forward current transfer ratio -10 160 -80 IB -0.5mA -0.4mA -60 120 -1 0.3m/ Ш -40 80 0.2mA -0.1 -20 40 0.1mA 0 -0.01 0 -0.1 0 -2 -4 -6 -8 -10 -12 -1 -3 -10 -30 -100 -300 -1000 -0.3 -1 Collector to emitter voltage V_{CE} (V) Collector current I_C (mA) Collector current Ic (mA) $C_{ob} - V_{CB}$ $V_{IN} - I_O$ 6 f=1MHz I_E=0 Ta=25°C -100 _E V₀=-0.2V Ta=25°C Collector output capacitance Cob (pF) 5 -10 Input voltage V_{IN} (V) -10 -0.1 4 3 ----

Output current Io (mA)

-0.3 -1 -3 -10 -30 -100

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2

1

0 L -1

-3

Collector to base voltage

-10

-30

V_{CB} (V)

-100

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